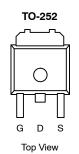
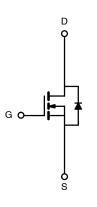
N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	I _D (A)		
60	0.016 @ V _{GS} = 10 V	40	



- TrenchFET[®] Power MOSFET
- 175°C Maximum Junction Temperature
- 100% Rg Tested





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25° C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60		
Gate-Source Voltage		V _{GS}	±20	- V	
	$T_{C} = 25^{\circ}C$	- I _D	40		
Continuous Drain Current (T _J = 175°C) ^b	$T_C = 125^{\circ}C$		30		
Pulsed Drain Current		I _{DM}	60	А	
Continuous Source Current (Diode Conduction)		۱ _S	40		
Avalanche Current		I _{AR}	40		
Repetitive Avalanche Energy (Duty Cycle \leq 1%)	L = 0.1 mH	E _{AR}	80	mJ	
	$T_{C} = 25^{\circ}C$	_	136 ^b		
Maximum Power Dissipation	$T_A = 25^{\circ}C$	P _D	3 ^a	w	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	$t \le 10 \text{ sec}$		15	18		
Junction-to-Ambient ^a	Steady State	R _{thJA}	40	50	°C/W	
Junction-to-Case		R _{thJC}	0.85	1.1		

Notes

a. Surface Mounted on 1" x1" FR4 Board.b. See SOA curve for voltage derating.

Parameter	Symbol	Test Condition	Min	Тур ^а	Max	Unit
Static			•			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = 250 μ A	60			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\;\mu A$	2.0		4.0	V
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 60 V, V_{GS} = 0 V, T_{J} = 125 $^{\circ}\text{C}$			50	μΑ
		V_{DS} = 60 V, V_{GS} = 0 V, T_{J} = 175 $^{\circ}\text{C}$			250	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	40			Α
		V_{GS} = 10 V, I_{D} = 40 A		0.013	0.016	
Drain-Source On-State Resistanceb	r _{DS(on)}	V_{GS} = 10 V, I_{D} = 40 A, T_{J} = 125°C			0.027	Ω
		V_{GS} = 10 V, I_D = 40 A, T_J = 175°C			0.037	
Forward Transconductanceb	9fs	V_{DS} = 15 V, I _D = 40 A		45		S
Dynamic ^a	· · ·					
Input Capacitance	C _{iss}			1960		pF
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 25 V, F = 1 MHz	-	370		
Reverse Transfer Capacitance	C _{rss}		-	200		
Total Gate Charge ^c	Qg			42	60	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 40 V, $~V_{GS}$ = 10 V, I_{D} = 40 A		7		nC
Gate-Drain Charge ^c	Q _{gd}			13		
Gate Resistance	Rg		0.5		2.7	Ω
Turn-On Delay Time ^c	t _{d(on)}			12	20	ns
Rise Time ^c	t _r	$V_{DD} = 40 \text{ V}, \text{ R}_{\text{I}} = 1.0 \Omega$		52	80	
Turn-Off Delay Time ^c	t _{d(off)}	$\begin{array}{l} V_{DD} = 40 \; V, \; R_L = 1.0 \; \Omega \\ I_D \; \cong \; 40 \; A, \; V_{GEN} = 10 \; V, \; R_g = 2.5 \; \Omega \end{array}$	-	25	38	
Fall Time ^c	t _f			10	15	
Source-Drain Diode Ratings and	d Characteristi	c (T _C = 25°C)				
Pulsed Current	I _{SM}				40	А
Diode Forward Voltage ^b	V _{SD}	$I_{F} = 40 \text{ A}, V_{GS} = 0 \text{ V}$		1.0	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 40 A, di/dt = 100 A/μs		45	70	ns

Notes

a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
c. Independent of operating temperature.



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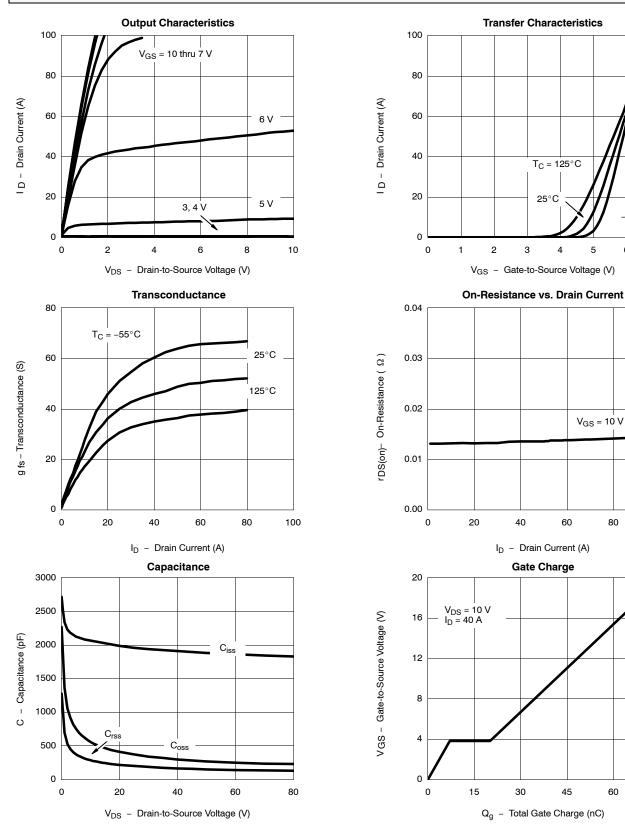
-55°C

7

100

6

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

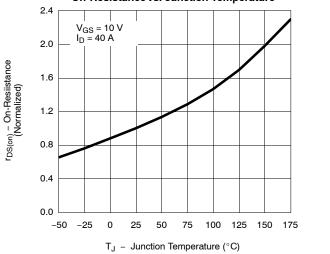


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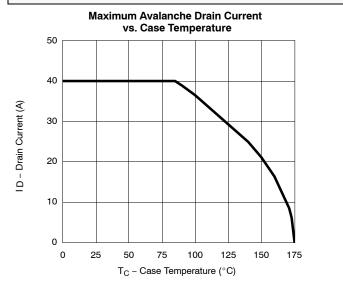


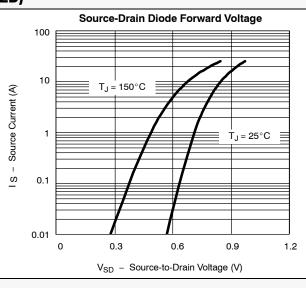
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THERMAL RATINGS

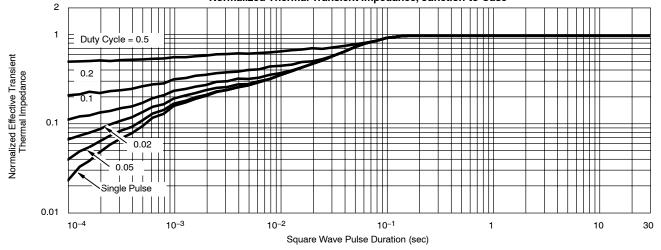




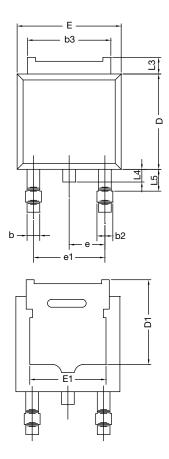
Safe Operating Area 1000 100 10 μs Limited by r_{DS(on)} 11 H 100 μs 10 1 ms 10 ms 100 ms 1 $T_C = 25^{\circ}C$ Ŧ ⊟1 s, dc Single Pulse 0.1 0.1 1 10 100 V_{DS} - Drain-to-Source Voltage (V)

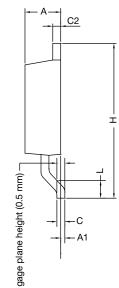


ID - Drain Current (A)



TO-252AA CASE OUTLINE





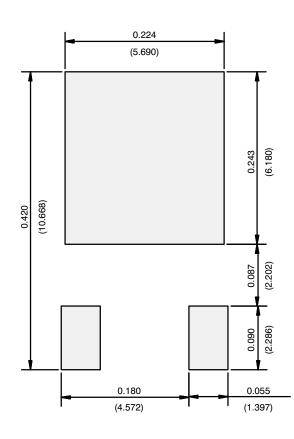
	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347					

Note

• Dimension L3 is for reference only.

<u>Din-Tek</u>

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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